AS23P06S-Q1

P-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-60V	47mΩ@-10V	-22.5A
	60mΩ@-4.5V	

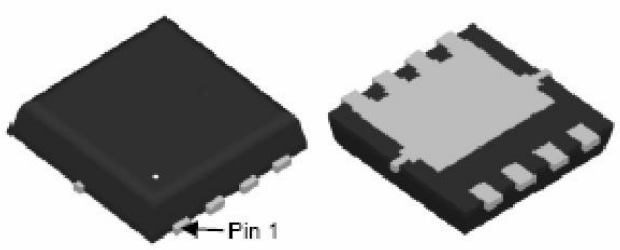
Feature

- High density cell design for ultra low Rdson
- High Speed switching
- Suffix"-Q1"for AEC-Q101

Application

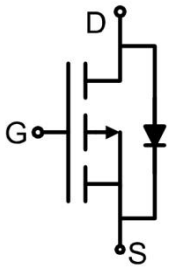
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Package



DFN3.3X3.3-8L

Circuit diagram



Marking

Absolute maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-22.5	A
Continuous Drain Current(T_C =100 ºC)	I_D (100 ºC)	-14.3	A
Pulsed Drain Current	I_{DM}	-90	A
Power Dissipation	P_D	43	W
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	2.9	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_A=25 ºC, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-60			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-60V,V_{GS} = 0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-1.3		-2.5	V
Drain-source on-resistance[1]	$R_{DS(on)}$	V_{GS} =-10V, I_D =-20A		35	47	mΩ
		V_{GS} =-4.5V, I_D =-10A		45	60	
Dynamic characteristics[2]						
Input Capacitance	C_{iss}	V_{DS} =-30V,V_{GS} =0V,f =1MHz		1100		pF
Output Capacitance	C_{oss}			350		
Reverse Transfer Capacitance	C_{rss}			28		
Total Gate Charge	Q_g	V_{DS} =-30V,V_{GS} =-10V, I_D =-20A		18.7		nC
Gate-Source Charge	Q_{gs}			4.7		
Gate-Drain Charge	Q_{gd}			3.0		
Turn-on delay time	$t_{d(on)}$	V_{DD}=-30V,V_{GS}=-10V, R_L =2.5Ω,R_{GEN}=6Ω		7.5		nS
Turn-on rise time	t_r			39.5		
Turn-off delay time	$t_{d(off)}$			43.6		
Turn-off fall time	t_f			55.1		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	V_{GS} =0V, I_S=-20A			-1.3	V
Diode Forward Current[1]	I_S				-23	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, I_F = -20A di/dt = 100A/μs [1]		20.2		nS
Reverse Recovery Charge	Q_{rr}			8.2		nC

Notes:

1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.

2) Guaranteed by design, not subject to production testing.

Typical Characteristics

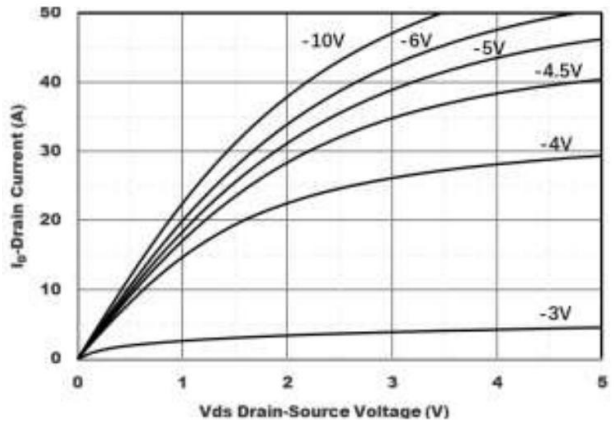


Figure1. Output Characteristics

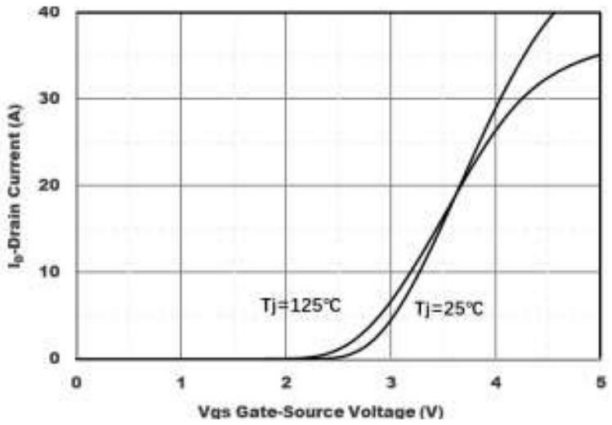


Figure2. Transfer Characteristics

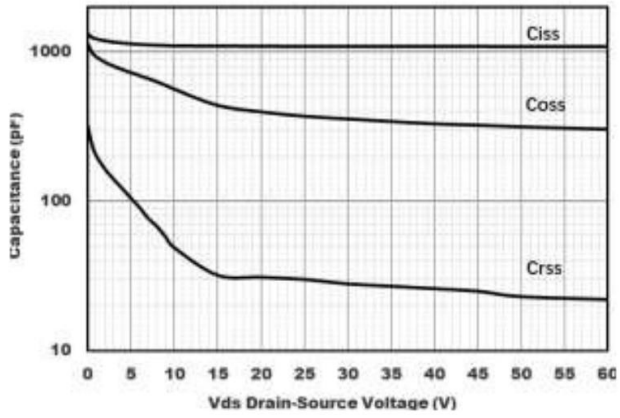


Figure3. Capacitance Characteristics

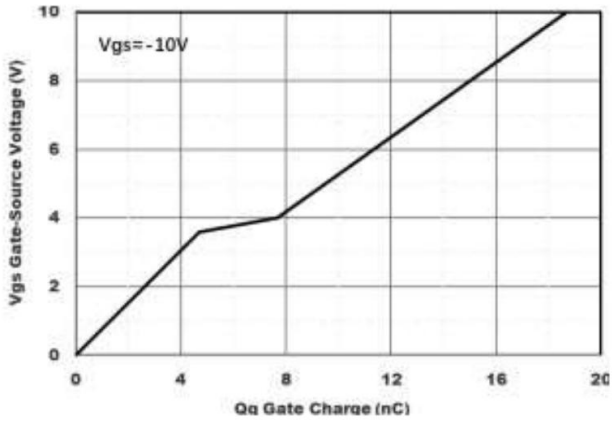


Figure4. Gate Charge

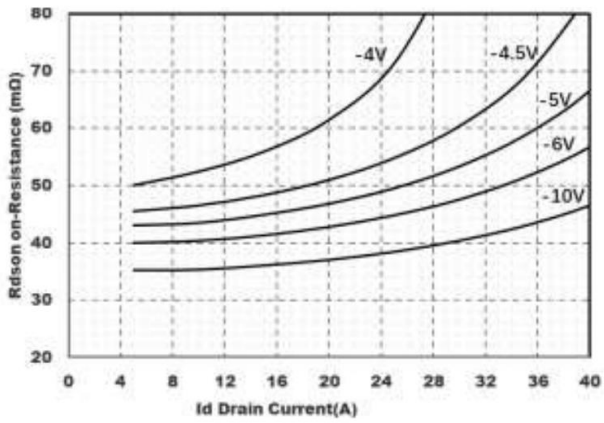


Figure5. : On-Resistance vs. Gate to Source Voltage

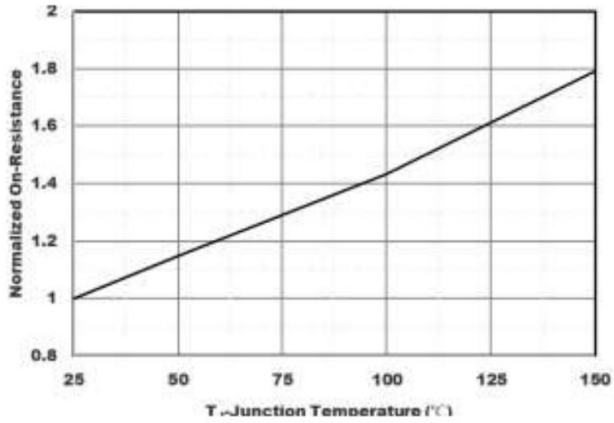


Figure6.Normalized On-Resistance

Typical Characteristics

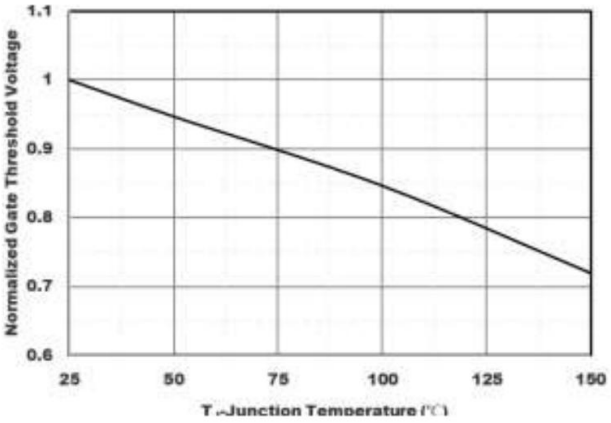


Figure7. Normalized Gate Threshold Voltage

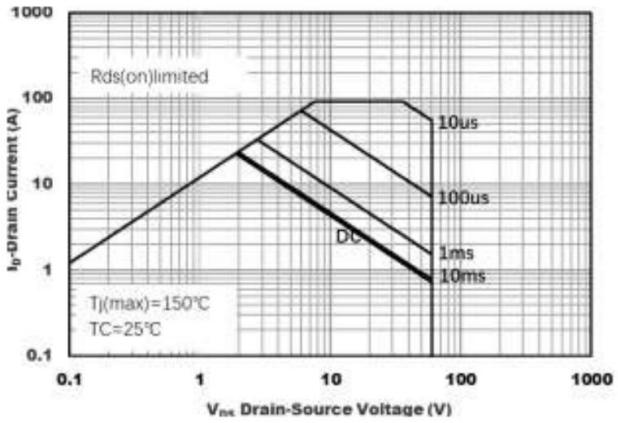


Figure8.Safe Operation Area

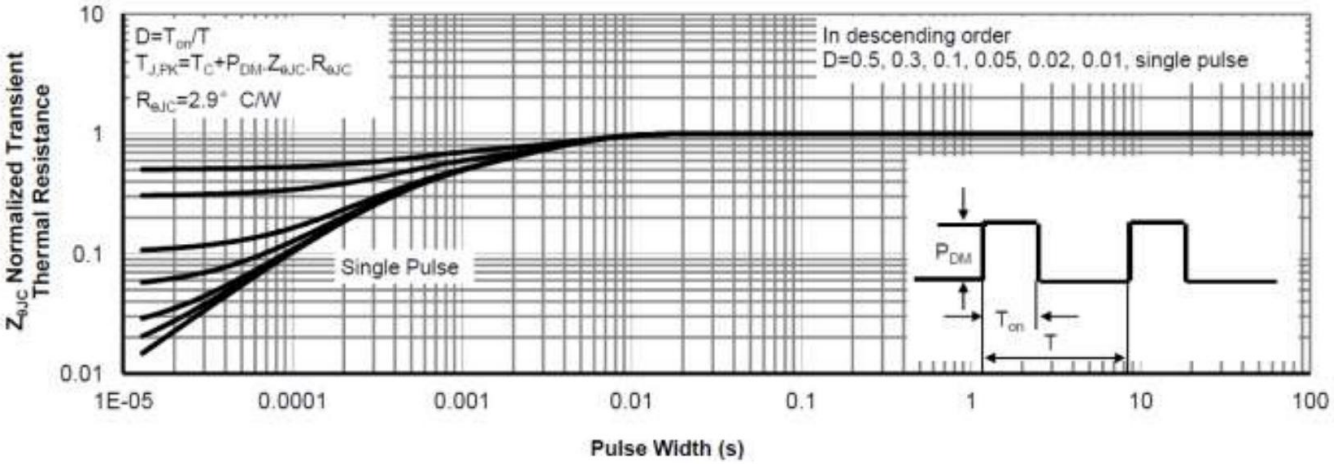
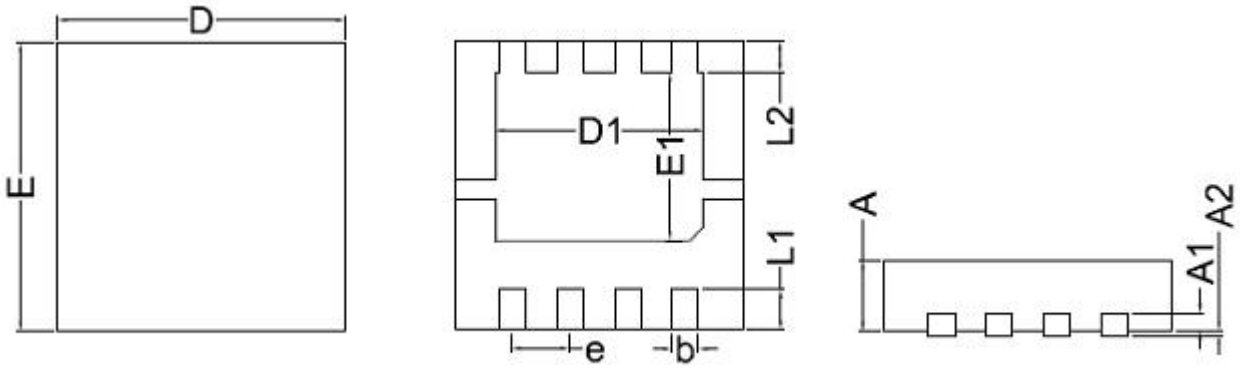


Figure9.Normalized Maximum Transient thermal impedance

DFN3.3X3.3-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.027	0.035
b	0.200	0.400	0.007	0.016
D	3.150	3.350	0.124	0.132
D1	2.200	2.500	0.086	0.098
E	3.150	3.350	0.124	0.132
E1	1.800	2.000	0.070	0.079
e	0.650 BSC		0.026 BSC	
A1	0.200 BSC		0.007 BSC	
A2	0.000	0.100	0.000	0.004
L1	0.350	0.550	0.013	0.022
L2	0.350 BCS.		0.013BSC	